IN

First Named Inventor	Leonard Forbes
Serial No.	10/808,058
Filing Date	March 24, 2004
Group Art Unit	2818
Examiner Name	Unknown
Confirmation No.	4217
Attorney Docket No.	400.288US01

# GENERAL TRANSMITTAL FORM UNDER 37 CFR 1.8 (LARGE ENTITY)

IIN 0 3 2005

Title: MEMORY DEVICE WITH HIGH DIELECTRIC CONSTANT GATE DIELECTRICS AND METAL FLOATING GATES

Mail Stop: AMENDMENT Commissioner for Patents

P. O. Box 1450

Alexandria, VA 22313-1450

#### **Enclosures**

#### The following documents are enclosed:

- X Supplemental Information Disclosure Statement (1 pg.); Form 1449 (1 pg.); 4 copies of cited references; U.S. reference(s) not included pursuant to 37 C.F.R. 1.98 (c)(2)(i);
- X An itemized return-receipt postcard

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# Please charge any additional fees or credit any overpayments to Deposit Account No. 501373.

#### **CUSTOMER NO. 27073**

#### **Submitted By** Kenneth W. Bolvin Name Reg. 34,125 (612) 312-2211 Telephone No. Signature Date Certificate of Mailing I certify that this correspondence and the identified documents listed on this transmittal are being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Mail Stop: AMENDMENT, Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450 on May 31, 2005. Name Kristen A. Smith Signature

(LARGE ENTITY TRANSMITTAL UNDER 37 CFR § 1.8)

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## SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

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In compliance with 37 C.F.R. §§ 1.56 and 1.97, et seq., the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified Application. Pursuant to 37 C.F.R. 1.98 (a)(2)(i), as this application was filed after June 30, 2003, Applicant has not included copies of U.S. Patents or U.S. Patent Applications. Applicant respectfully requests that this Supplemental Information Disclosure Statement be entered and the references listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to MPEP §609, Applicant further requests that the Examiner initial next to each reference on the Form 1449 to indicate that the listed references have been considered. Applicant further requests that a copy of the initialed Form 1449 be returned with the next official communication.

As an Office Action has not yet issued in this application, Applicant believes that no fees are due. However, the Commissioner for Patents is hereby authorized to charge any additional fees to Deposit Account No. 501373.

If the Examiner has any questions or concerns regarding this application, please contact the undersigned at (612) 312-2211.

Respectfully submitted,

Data

Kenneth W. Bolvin

Reg. No. 34,125

Attorneys for Applicant Leffert Jay & Polglaze P.O. Box 581009 Minneapolis, MN 55458-1009 T 612 312-2200 F 612 312-2250

First Named Inventor	Leonard Forbes		
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### SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT FORM PTO-1449

Title: MEMORY DEVICE WITH HIGH DIELECTRIC CONSTANT GATE DIELECTRICS AND METAL FLOATING GATES Sheet 1 of 1

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Initials	Country	No.		Date	

Other References
Author, Title, Date, Pages, etc.
Min She et al., 19th IEEE Non-Volatile Semiconductor Memory Workshop 2003, p. 53-55, "Improved SONOS-type Flash Memory Using HfO <sub>2</sub> as Trapping Layer"
Shin et al., 19th IEEE Non-Volatile Semiconductor Memory Workshop 2003, p. 58-59, "High Reliable SONOS-type NAND Flash Memory Cell with Al <sub>2</sub> O <sub>3</sub> for Top Oxide"
Blomme et al., 19th IEEE Non-Volatile Semiconductor Memory Workshop 2003, p. 93-94, "A Novel Low Voltage Memory Device with an Engineered SiO <sub>2</sub> /high-k tunneling barrier"
Lusky et al., (November) 2001, <i>IEEE Electron Device Letters</i> , Volume 22, No. 11, p. 556-558, "Characterization of Channel Hot Electron Injection by the Subthreshold Slope"

Examiner		Date		
Signature		Considered		
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not				
in conformance and not considered. Include copy of this form with next communication to applicant.				